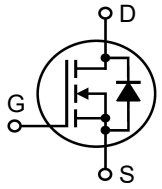
IXYS

X3-Class HiPerFET™ Power MOSFET

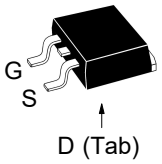
IXFA36N60X3

V_{DSS} = 600V
I_{D25} = 36A
$R_{DS(on)}$ ≤ 90mΩ

N-Channel Enhancement Mode
Avalanche Rated



TO-263 (IXFA)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	600	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	600	V
V_{GSS}	Continuous	±20	V
V_{GSM}	Transient	±30	V
I_{D25}	T_C = 25°C	36	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	48	A
I_A	T_C = 25°C	8	A
E_{AS}	T_C = 25°C	750	mJ
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, $T_J \le 150°C$	50	V/ns
P_D	T_C = 25°C	446	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_{SOLD}	Plastic Body for 10s	260	°C
F_C	Mounting Force	10..65 / 2.2..14.6	N/lb
Weight		2.5	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = 1mA	600			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 2.5mA	3.5		5.0	V
I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			25	μA
	T_J = 125°C			1	mA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			90	mΩ

Features

- International Standard Package
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
g_{fs}	V_{DS} = 10V, I_D = 0.5 • I_{D25}, Note 1	16	26		S
R_{Gi}	Gate Input Resistance		2.1		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		2030		pF
C_{oss}			3050		pF
C_{rss}			3.6		pF
	Effective Output Capacitance				
$C_{o(er)}$	Energy related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		110		pF
$C_{o(tr)}$	Time related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		510		pF
$t_{d(on)}$	**Resistive Switching Times**		23		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		8		ns
$t_{d(off)}$	R_G = 10Ω (External)		45		ns
t_f			4		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		29		nC
Q_{gs}			10		nC
Q_{gd}			10		nC
R_{thJC}				0.28	°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
I_S	V_{GS} = 0V			36	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			144	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 18A, -di/dt = 100A/μs		180		ns
Q_{RM}	V_R = 100V		1.6		μC
I_{RM}			18.0		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

Fig. 1. Output Characteristics @ T_J = 25ºC

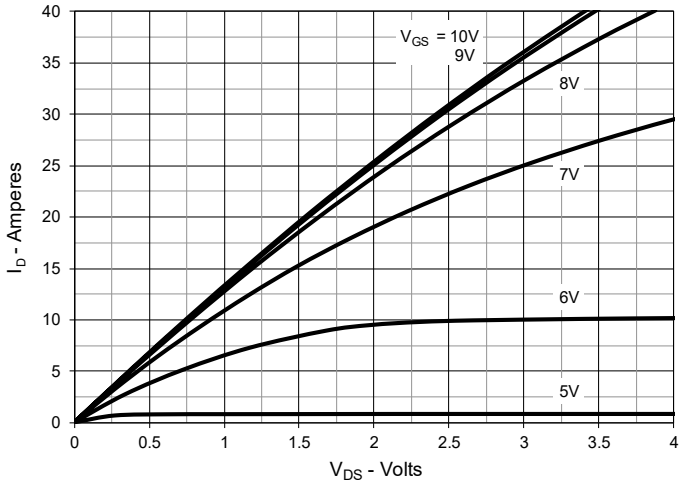


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

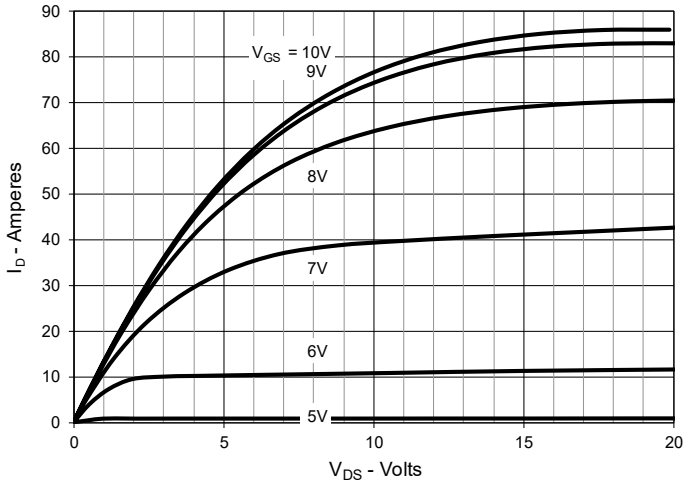


Fig. 3. Output Characteristics @ T_J = 125ºC

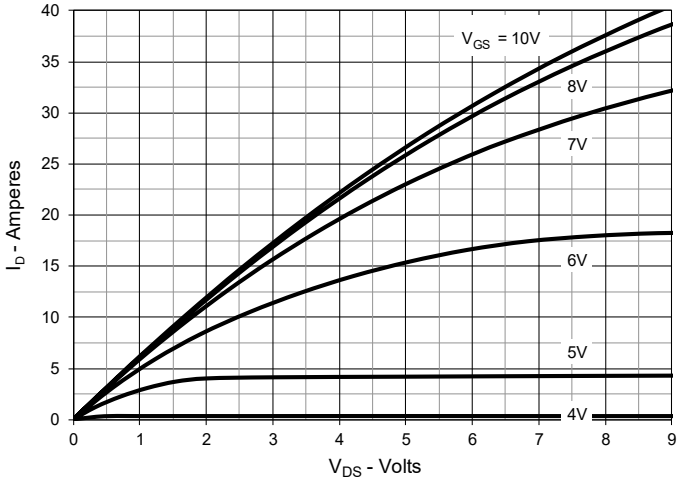


Fig. 4. $R_{DS(on)}$ Normalized to I_D = 18A Value vs. Junction Temperature

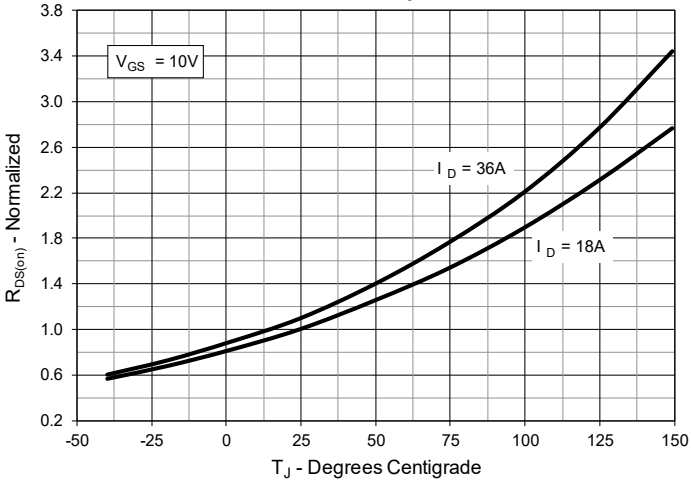


Fig. 5. $R_{DS(on)}$ Normalized to I_D = 18A Value vs. Drain Current

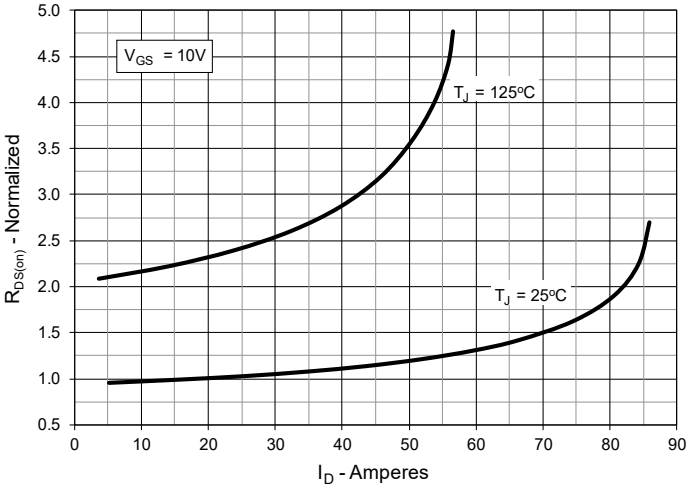


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

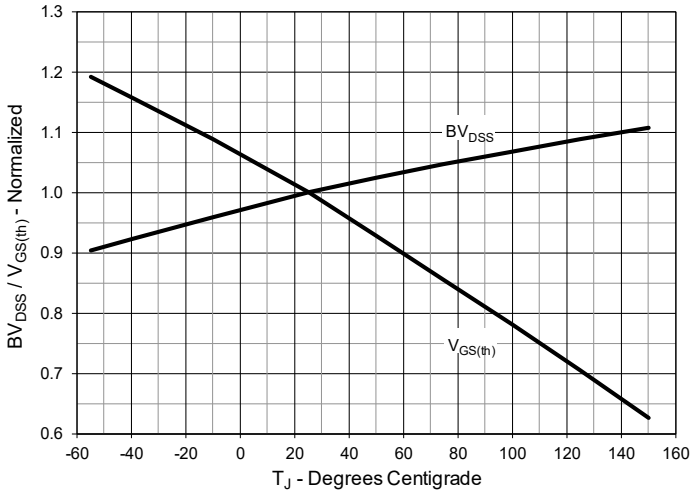


Fig. 7. Maximum Drain Current vs. Case Temperature

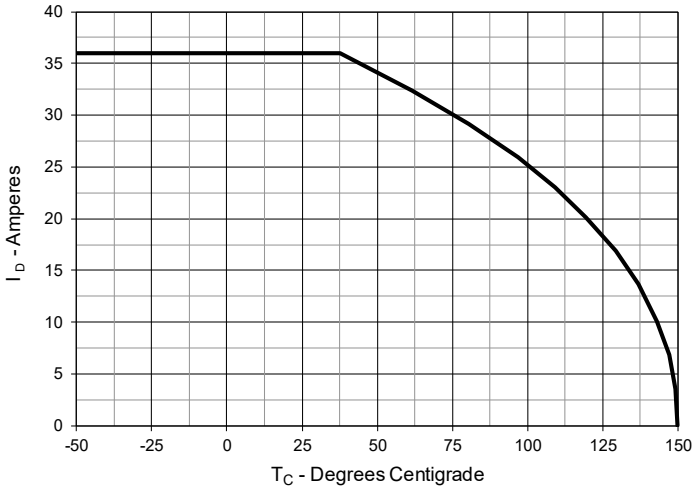


Fig. 8. Input Admittance

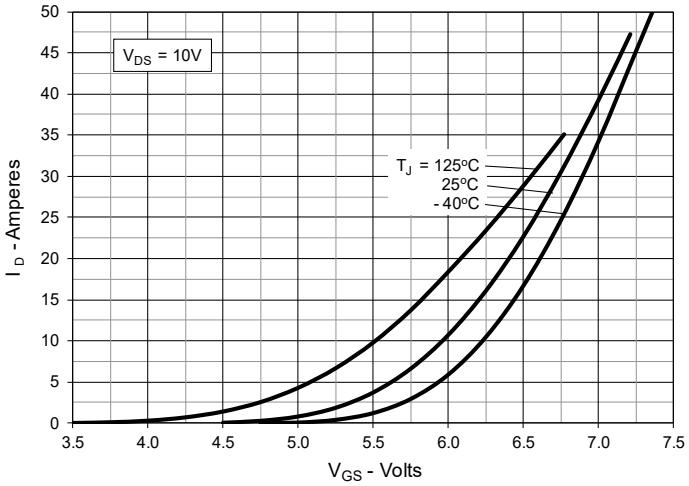


Fig. 9. Transconductance

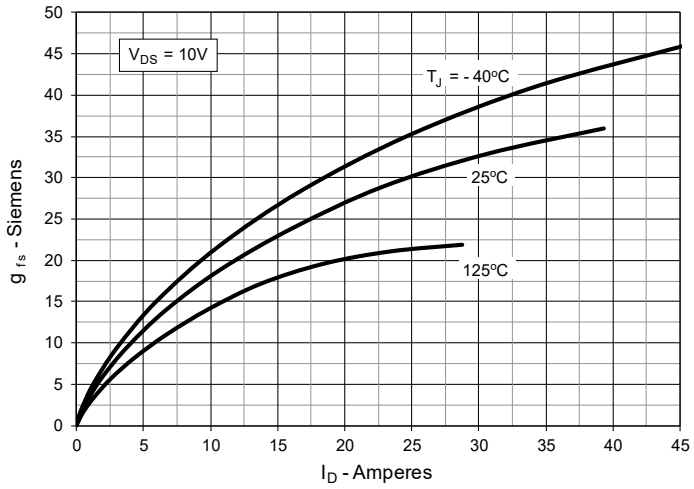


Fig. 10. Forward Voltage Drop of Intrinsic Diode

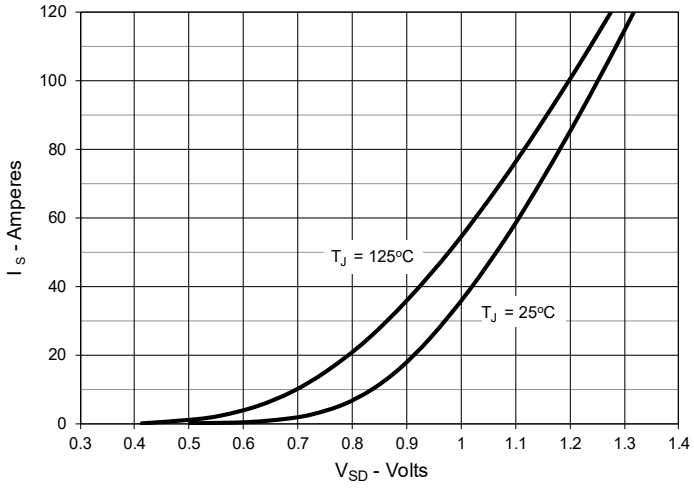


Fig. 11. Gate Charge

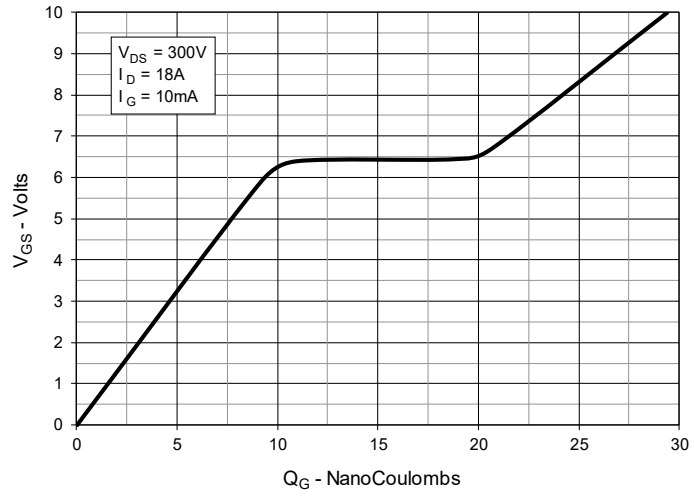


Fig. 12. Capacitance

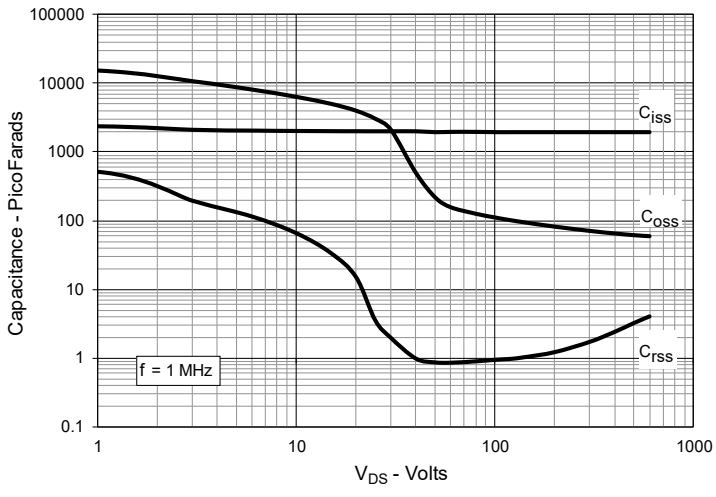


Fig. 13. Output Capacitance Stored Energy

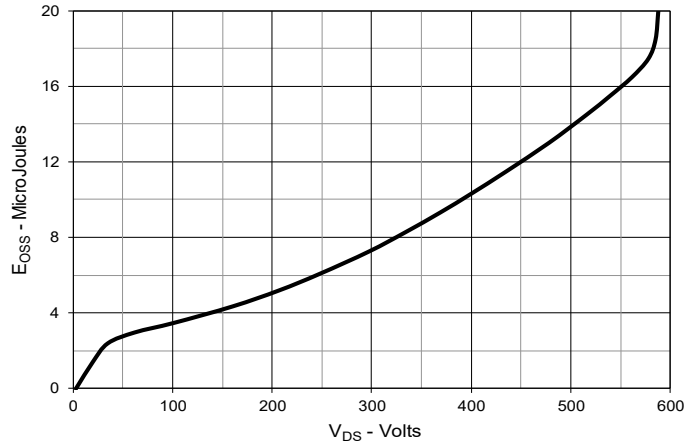


Fig. 14. Forward-Bias Safe Operating Area

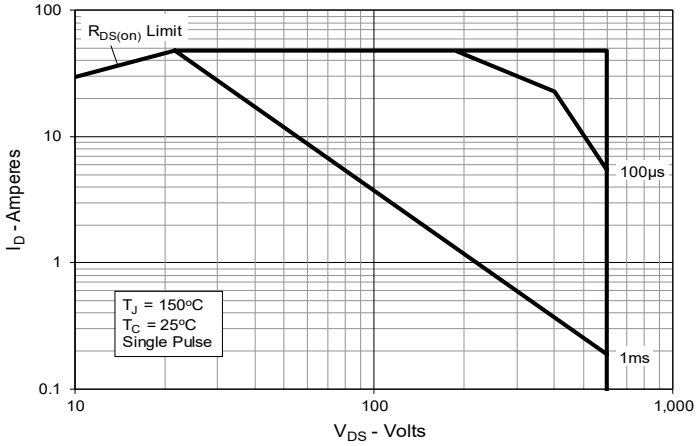
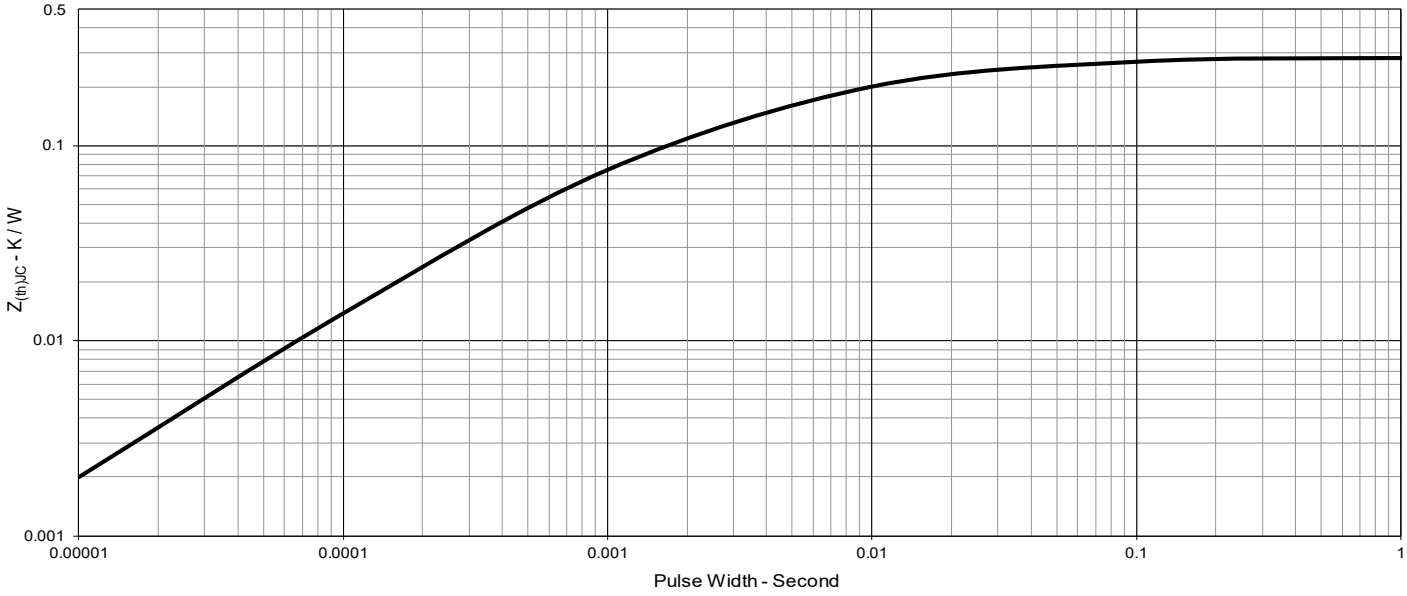
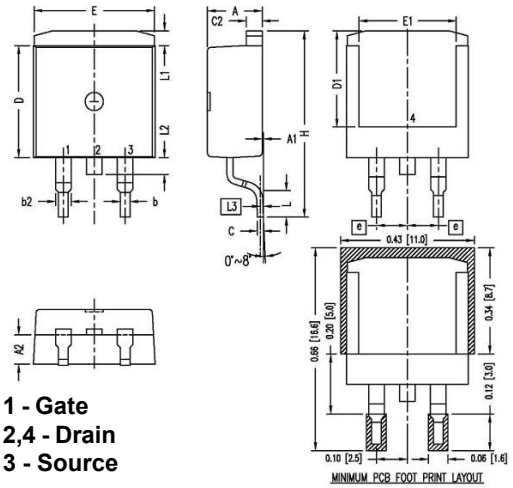


Fig. 15. Maximum Transient Thermal Impedance



TO-263 Outline



1 - Gate
2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
e	.100 BSC		2.54 BSC	
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
L3	.010 BSC		0.254 BSC	

NOTE:
1. This drawing meets all dimensions requirement of JEDEC outlines TO-263AB.
2. All metal surface are matte pure tin plated except trimmed area.
3. L3 is Gauge plane to measure L.
4. These dimension do not include mold flash and they will not exceed 0.005[0.13] per side.

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